



General description

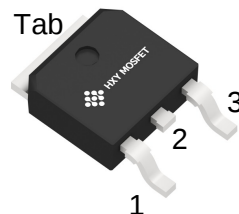
INN700TK190B is a 725V GaN-on-Si enhancement-mode power transistor in TO-252-2L package. The properties of GaN allow for high current, high breakdown voltage and high switching frequency. The TO-252-2L package offers low parasitic inductance, strong heat dissipation capability and high solderability, which make GaN better apply to consumer and industrial applications.

Features

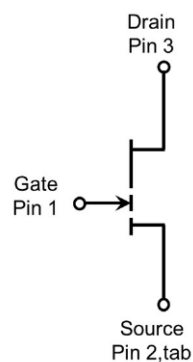
- 725V GaN enhancement-mode power switch
- $R_{DS(on), max}$ 200m Ω
- Gate recommend drive voltage 0V - 6V
- Ultra-low FOM
- Ultra-high switching frequency
- Reverse current capability
- Zero reverse recovery loss Monolithic
- integrated ESD protection
- RoHS, Pb-free, REACH-compliant

Applications

- AC-DC converters
- DC-DC converters
- Totem pole PFC
- Fast charging
- Power adapters
- LED lighting drivers
- Wireless power transfer
- Laser drivers
- TV display



TO-252-2L



Gate	1
Source	2, tab
Drain	3



Maximum ratings

at $T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified. Continuous application of maximum ratings can deteriorate transistor lifetime.
For further information, contact CloudSemi sales office.

Table 3 Maximum rating

Parameters	Symbols	Values			Units	Notes/Test Conditions
		Min.	Typ.	Max.		
Drain-source voltage	$V_{DS, \max}$	-	-	725	V	$V_{GS} = 0\text{ V}$, $I_D = 10\text{ }\mu\text{A}$
Drain-source voltage transient ¹	$V_{DS, \text{transient}}$	-	-	850	V	$V_{GS} = 0\text{ V}$, $V_{DS} = 850\text{ V}$
Continuous current, drain-source	I_D	-	-	10	A	$T_c = 25\text{ }^{\circ}\text{C}$
Pulsed current, drain-source ²	$I_{D, \text{pulse}}$	-	-	18	A	$T_c = 25\text{ }^{\circ}\text{C}$; $V_G = 6\text{ V}$
Pulsed current, drain-source ²	$I_{D, \text{pulse}}$	-	-	10	A	$T_c = 125\text{ }^{\circ}\text{C}$; $V_G = 6\text{ V}$
Gate-source voltage, continuous	V_{GS}	-1.4	-	+7	V	$T_j = -55\text{ }^{\circ}\text{C}$ to $150\text{ }^{\circ}\text{C}$
Gate-source voltage, pulsed	$V_{GS, \text{pulse}}$	-	-	+10	V	$T_j = -55\text{ }^{\circ}\text{C}$ to $150\text{ }^{\circ}\text{C}$; $t_{\text{Pulse}} = 50\text{ ns}$, $f = 100\text{ kHz}$; open drain
Power dissipation	P_{tot}	-	-	73	W	$T_c = 25\text{ }^{\circ}\text{C}$
Operating temperature	T_j	-55	-	+150	$^{\circ}\text{C}$	
Storage temperature	T_{stg}	-55	-	+150	$^{\circ}\text{C}$	

1. $V_{DS, \text{transient}}$ is intended for surge rating during non-repetitive events, $t_{\text{Pulse}} < 1\text{ }\mu\text{s}$.

2. Pulse width = $10\text{ }\mu\text{s}$.

Thermal characteristics

Table 4 Thermal characteristics

Parameters	Symbols	Values			Units	Notes/Test Conditions
		Min.	Typ.	Max.		
Thermal resistance, junction-case	R_{thJC}	-	-	1.7	$^{\circ}\text{C/W}$	
Reflow soldering temperature	T_{sold}	-	-	260	$^{\circ}\text{C}$	MSL3



Electrical characteristics

at $T_j = 25\text{ }^{\circ}\text{C}$, unless specified otherwise.

Table 5 Static characteristics

Parameters	Symbols	Values			Units	Notes/Test Conditions
		Min.	Typ.	Max.		
Gate threshold voltage	$V_{GS(TH)}$	1.2	1.6	2.5	V	$I_D = 11\text{ mA}$; $V_{DS} = V_{GS}$; $T_j = 25\text{ }^{\circ}\text{C}$
		-	1.6	-		$I_D = 11\text{ mA}$; $V_{DS} = V_{GS}$; $T_j = 125\text{ }^{\circ}\text{C}$
Drain-source leakage current	I_{DSS}	-	4	50	μA	$V_{DS} = 725\text{ V}$; $V_{GS} = 0\text{ V}$; $T_j = 25\text{ }^{\circ}\text{C}$
		-	10	-		$V_{DS} = 725\text{ V}$; $V_{GS} = 0\text{ V}$; $T_j = 125\text{ }^{\circ}\text{C}$
Gate-source leakage current	I_{GSS}	-	-	200	μA	$V_{GS} = 6\text{ V}$; $V_{DS} = 0\text{ V}$
Drain-source on-state resistance	$R_{DS(on)}$	-	160	200	$\text{m}\Omega$	$V_{GS} = 6\text{ V}$; $I_D = 3\text{ A}$; $T_j = 25\text{ }^{\circ}\text{C}$
		-	330	-	$\text{m}\Omega$	$V_{GS} = 6\text{ V}$; $I_D = 3\text{ A}$; $T_j = 125\text{ }^{\circ}\text{C}$
Gate resistance	R_G	-	3.5	-	Ω	$f = 5\text{ MHz}$; open drain

Table 6 Dynamic characteristics

Parameters	Symbols	Values			Units	Notes/Test Conditions
		Min.	Typ.	Max.		
Input capacitance	C_{iss}	-	83	-	pF	$V_{GS} = 0\text{ V}$; $V_{DS} = 400\text{ V}$; $f = 1\text{ MHz}$
Output capacitance	C_{oss}	-	27	-	pF	$V_{GS} = 0\text{ V}$; $V_{DS} = 400\text{ V}$; $f = 1\text{ MHz}$
Reverse transfer capacitance	C_{rss}	-	0.4	-	pF	$V_{GS} = 0\text{ V}$; $V_{DS} = 400\text{ V}$; $f = 1\text{ MHz}$
Effective output capacitance, energy related ¹	$C_{o(er)}$	-	35	-	pF	$V_{GS} = 0\text{ V}$; $V_{DS} = 0\text{ to }400\text{ V}$
Effective output capacitance, time related ²	$C_{o(tr)}$	-	54	-	pF	$V_{GS} = 0\text{ V}$; $V_{DS} = 0\text{ to }400\text{ V}$
Output charge	Q_{oss}	-	22	-	nC	$V_{GS} = 0\text{ V}$; $V_{DS} = 0\text{ to }400\text{ V}$
Turn-on delay time	$t_{d(on)}$	-	2	-	ns	$V_{DS} = 400\text{ V}$; $I_D = 6\text{ A}$; $L = 318\text{ }\mu\text{H}$; $V_{GS} = 6\text{ V}$; $R_{on} = 10\text{ }\Omega$; $R_{off} = 2\text{ }\Omega$
Turn-off delay time	$t_{d(off)}$	-	4	-	ns	
Rise time	t_r	-	5	-	ns	
Fall time	t_f	-	6	-	ns	

1. $C_{o(er)}$ is the fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 400 V.

2. $C_{o(tr)}$ is the fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 400 V.



Table 7 Gate charge characteristics

Parameters	Symbols	Values			Units	Notes/Test Conditions
		Min.	Typ.	Max.		
Gate charge	Q_G	-	2.3	-	nC	$V_{GS} = 0 \text{ to } 6 \text{ V}; V_{DS} = 400 \text{ V};$ $I_D = 3 \text{ A}$
Gate-source charge	Q_{GS}	-	0.2	-	nC	
Gate-drain charge	Q_{GD}	-	0.9	-	nC	
Gate plateau voltage	V_{plat}	-	2.4	-	V	$V_{DS} = 400 \text{ V}; I_D = 3 \text{ A}$

Table 8 Reverse conduction characteristics

Parameters	Symbols	Values			Units	Notes/Test Conditions
		Min.	Typ.	Max.		
Source-drain reverse voltage	V_{SD}	-	2.5	-	V	$V_{GS} = 0 \text{ V}; I_{SD} = 3 \text{ A}$
Pulsed current, reverse	$I_{S, pulse}$	-	20	-	A	$V_{GS} = 6 \text{ V}$
Reverse recovery charge ¹	Q_{rr}	-	0	-	nC	$I_{SD} = 3 \text{ A}; V_{DS} = 400 \text{ V}$
Reverse recovery time	t_{rr}	-	0	-	ns	
Peak reverse recovery current	I_{rrm}	-	0	-	A	

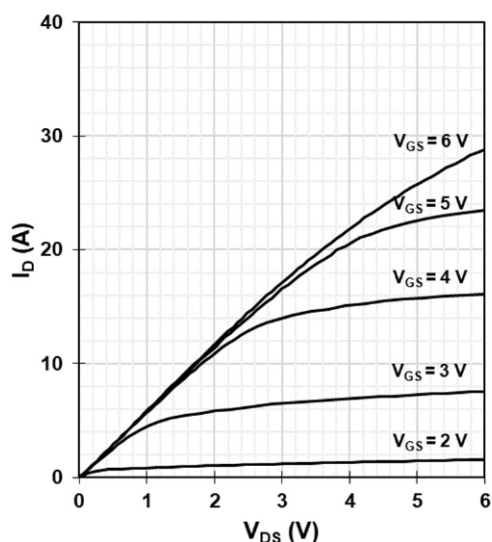
1. Excluding Q_{OSS}



Electrical characteristics diagrams

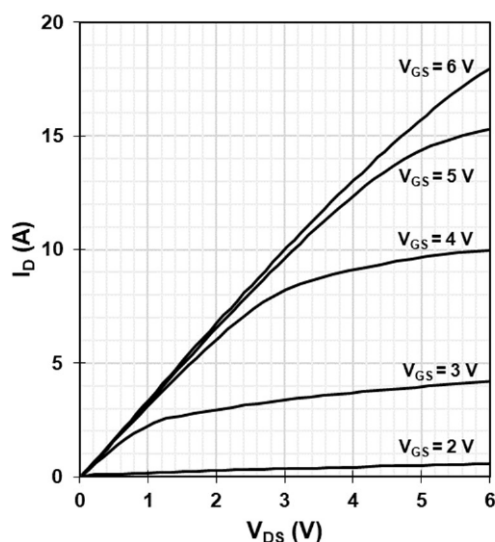
at $T_j = 25\text{ }^{\circ}\text{C}$, unless specified otherwise.

Figure 1 Typ. output characteristics



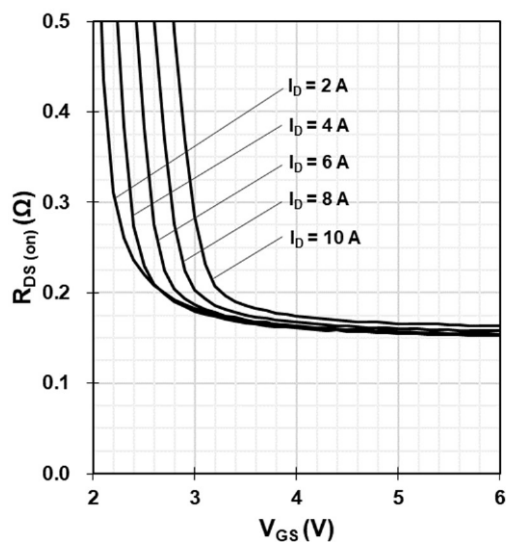
$$I_D = f(V_{DS}, V_{GS}); T_j = 25\text{ }^{\circ}\text{C}$$

Figure 2 Typ. output characteristics



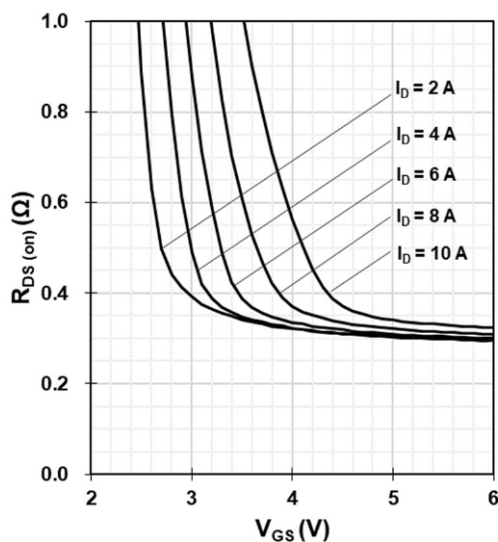
$$I_D = f(V_{DS}, V_{GS}); T_j = 125\text{ }^{\circ}\text{C}$$

Figure 3 Typ. drain-source on-state resistance



$$R_{DS(on)} = f(I_D, V_{GS}); T_j = 25\text{ }^{\circ}\text{C}$$

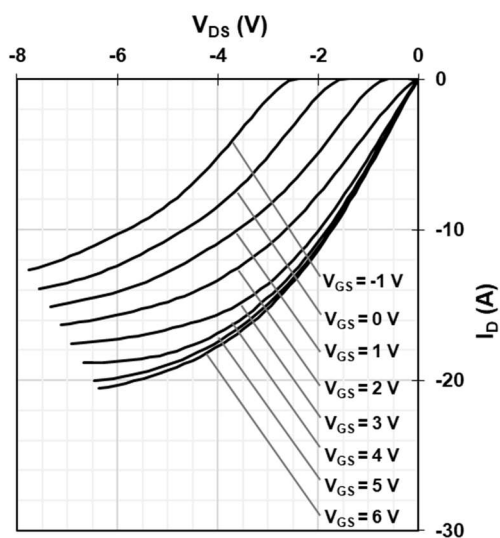
Figure 4 Typ. drain-source on-state resistance



$$R_{DS(on)} = f(I_D, V_{GS}); T_j = 125\text{ }^{\circ}\text{C}$$

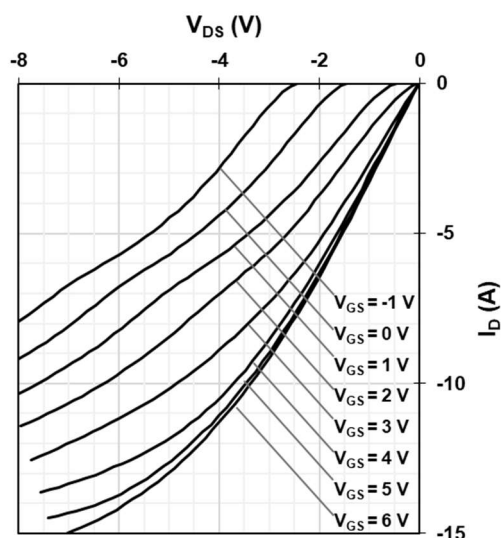


Figure 5 Typ. channel reverse characteristics



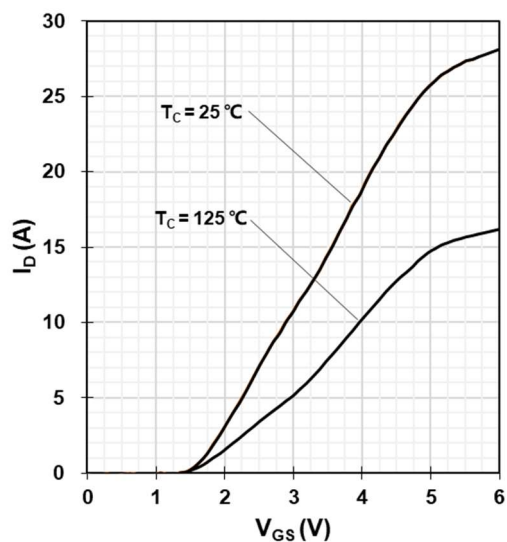
$$I_D = f(V_{DS}, V_{GS}); T_J = 25^\circ\text{C}$$

Figure 6 Typ. channel reverse characteristics



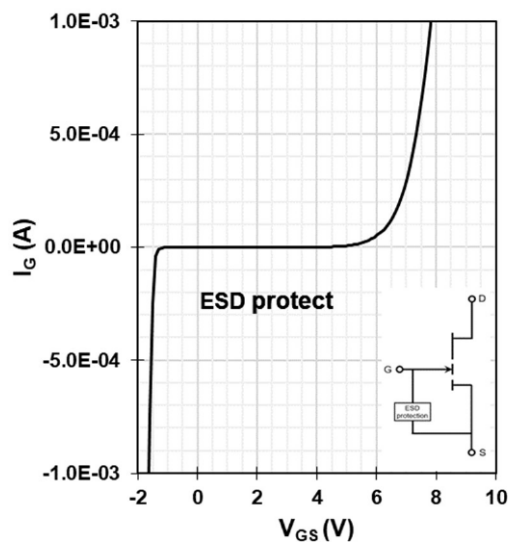
$$I_D = f(V_{DS}, V_{GS}); T_J = 125^\circ\text{C}$$

Figure 7 Typ. transfer characteristics



$$I_D = f(V_{GS}); V_{DS} = 5\text{ V}$$

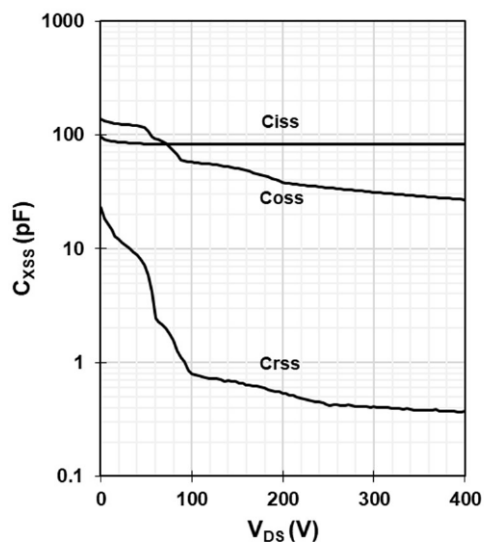
Figure 8 Typ. gate-to-source leakage



$$I_G = f(V_{GS}); V_D = \text{open}$$

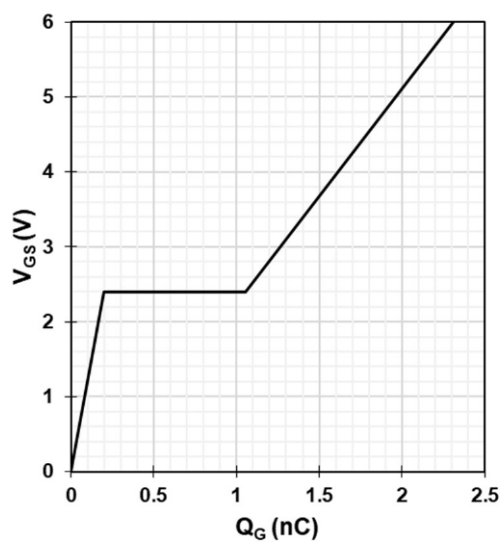


Figure 9 Typ. capacitances



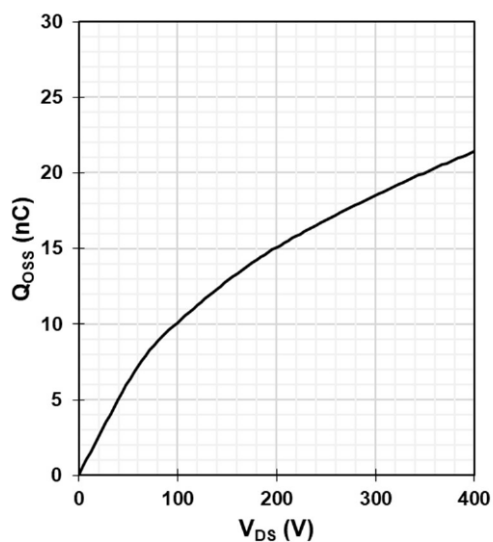
$C_{XSS} = f(V_{DS})$; Freq. = 1 MHz

Figure 10 Typ. gate charge



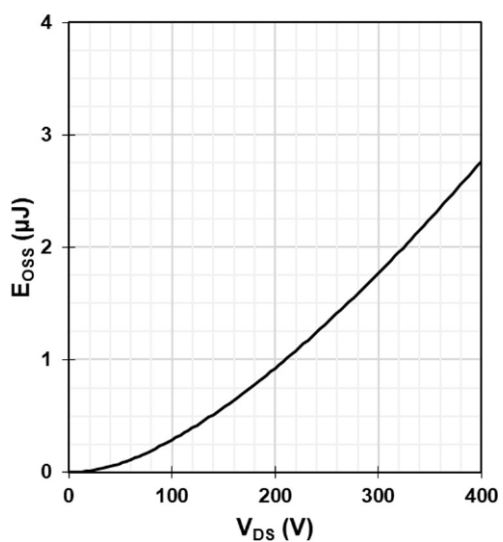
$V_{GS} = f(Q_G)$; $V_{DS} = 400$ V; $I_D = 3$ A

Figure 11 Typ. output charge



$Q_{OSS} = f(V_{DS})$; Freq. = 1 MHz

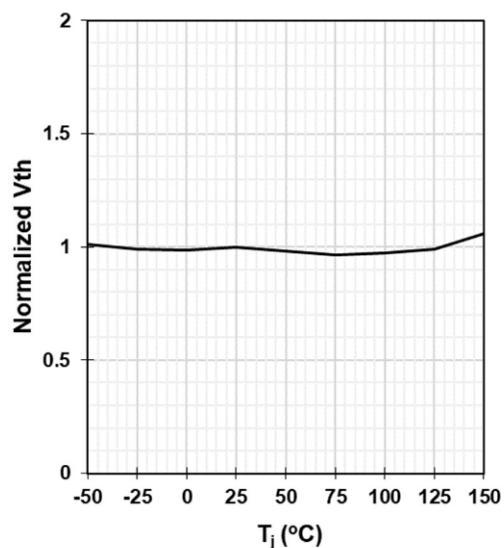
Figure 12 Typ. C_{OSS} stored energy



$E_{OSS} = f(V_{DS})$; Freq. = 1 MHz

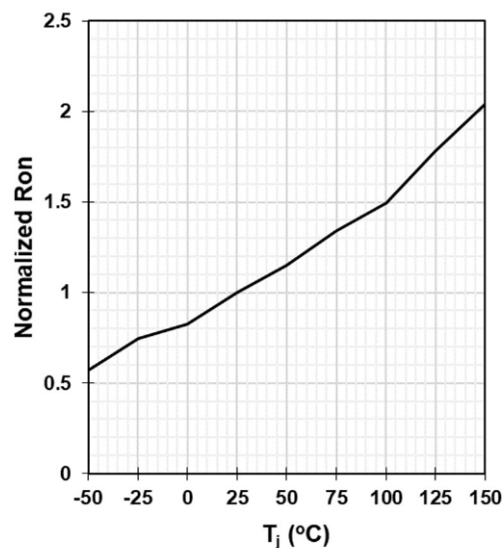


Figure 13 Gate threshold voltage



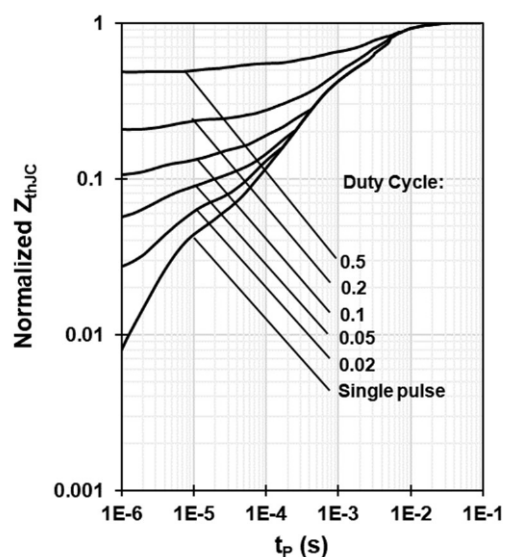
$$V_{GS(TH)} = f(T_j); V_{GS} = V_{DS}; I_D = 11 \text{ mA}$$

Figure 14 Drain-source on-state resistance



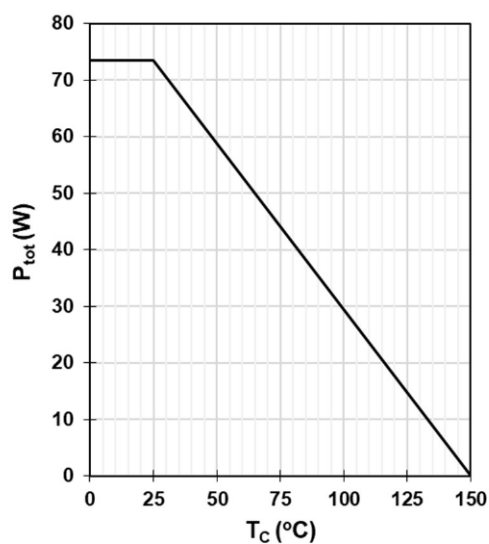
$$R_{DS(on)} = f(T_j); I_D = 3 \text{ A}; V_{GS} = 6 \text{ V}$$

Figure 15 Max. transient thermal impedance



$$Z_{thJC} = f(t_p, D)$$

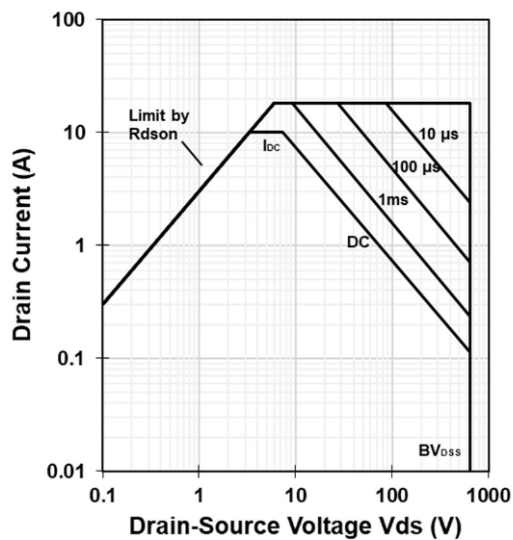
Figure 16 Power dissipation



$$P_{tot} = f(T_c)$$

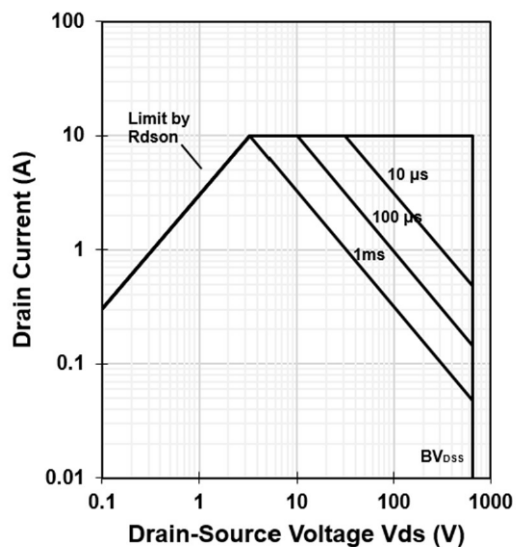


Figure 17 Safe operating area



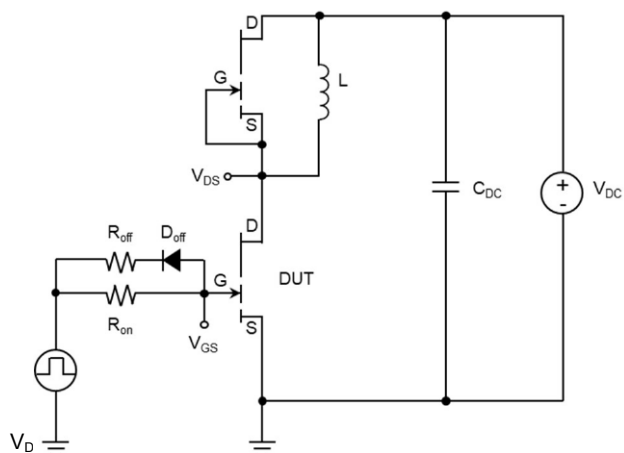
$$I_D = f(V_{DS}); T_C = 25\text{ }^{\circ}\text{C}$$

Figure 18 Safe operating area



$$I_D = f(V_{DS}); T_C = 125\text{ }^{\circ}\text{C}$$

Figure 19 Switching time test circuit

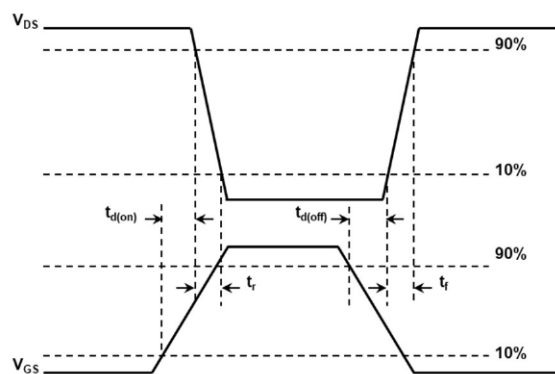


$$R_{on} = 10\text{ }\Omega, R_{off} = 2\text{ }\Omega$$

$$V_{DS} = 400\text{ V}, I_D = 6\text{ A}, L = 318\text{ }\mu\text{H}, V_{GS} = 6\text{ V},$$

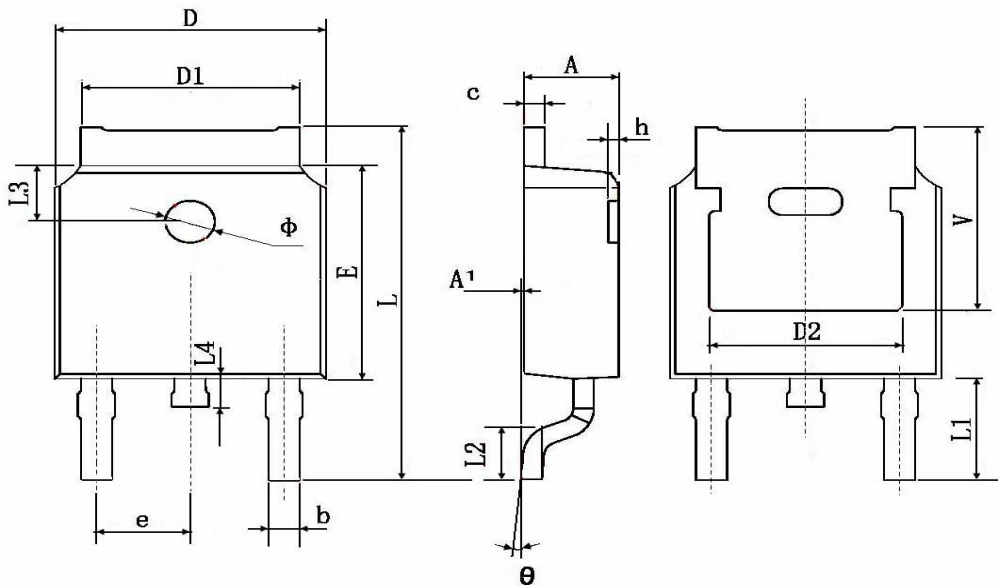
$$R_{on} = 10\text{ }\Omega, R_{off} = 2\text{ }\Omega$$

Figure 20 Typ. switching time waveforms





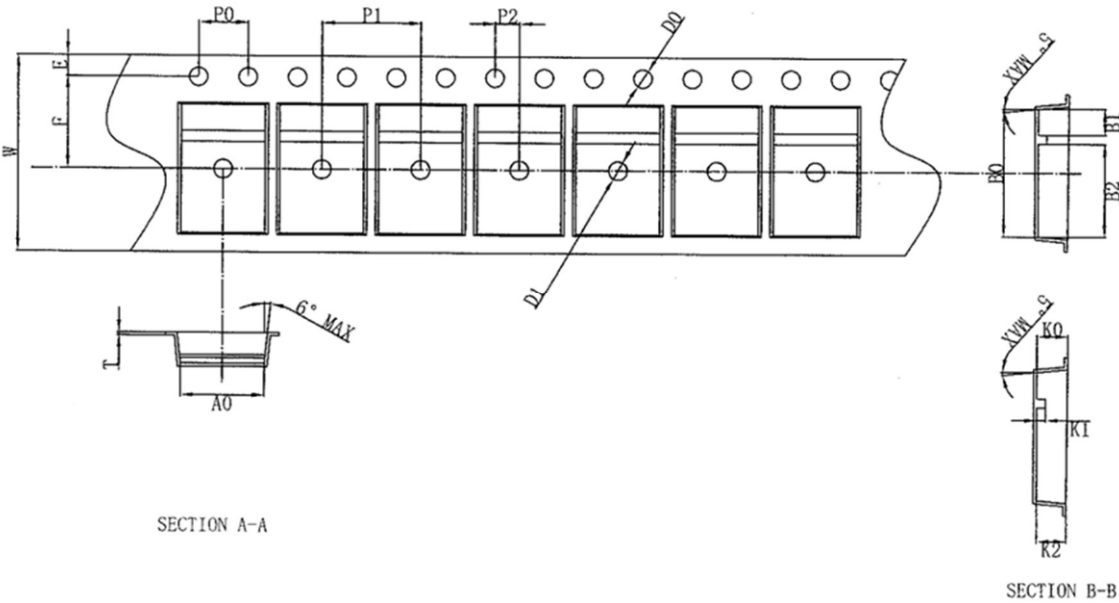
Package outlines
TO-252-2L



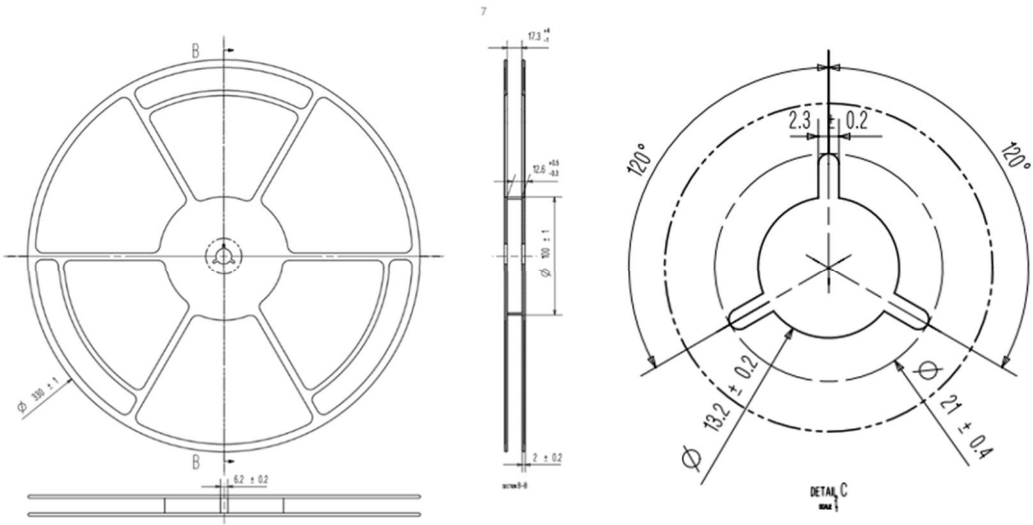
Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830 TYP.		0.190 TYP.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 TYP.		0.114 TYP.	
L2	1.400	1.700	0.055	0.067
L3	1.600 TYP.		0.063 TYP.	
L4	0.600	1.000	0.024	0.039
Φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.350 TYP.		0.211 TYP.	



Reel information



SYMBOL	DIMENSION	SYMBOL	DIMENSION
W	16.00±0.30	10P0	40.00±0.20
E	1.75±0.10	P1	8.00±0.10
F	7.50±0.05	A0	6.80±0.10
D0	1.625±0.125	B0	10.40±0.10
D1	1.55±0.05	K0	2.5±0.10
P0	4.00±0.10	T	0.25±0.05
P2	2.00±0.10	K1	0.70±0.05
B1	2.10±0.05	K2	2.40±0.10
B2	7.55±0.05		





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